Schottky Barrier Rectifier, Trench-based

NRTS1260PFS, NRVTS1260PFS

This TO-277 trench Schottky rectifier provides fast switching performance in a compact thermally efficient package. The TO-277 package provides an excellent alternative to the DPAK, offering thermal performance nearly as good in a package occupying less than half the board space. Its low profile makes it a good option for flat panel display and other applications with limited vertical clearance. The device offers low leakage over temperature making it a good match for applications requiring low quiescent current.

Features

- Package Provides Capability of Inspection and Probe After Board Mounting
- Low Forward Voltage Drop
- 175°C Operating Junction Temperature
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

Applications

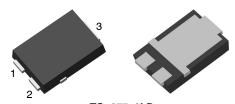
- Excellent Alternative to DPAK in Space-Constrained Automotive Applications
- Low Leakage for Higher Temperature Operation
- Output Rectification in Compact Portable Consumer Applications
- Freewheeling Diode used with Inductive Loads



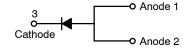
ON Semiconductor®

www.onsemi.com

SCHOTTKY BARRIER RECTIFIER, 12 AMPERES 60 VOLTS



TO-277-3LD CASE 340CZ



MARKING DIAGRAM

TS1260 AWLYW

TS1260 = Specific Device Code A = Assembly Location

′ = Year

W = Work Week
WL = Wafer Lot

ORDERING INFORMATION

	Device	Package	Shipping†
	NRTS1260PFST3G	TO-277 (Pb-Free)	1500 / Tape & Reel
Ī	NRVTS1260PFST3G	TO-277 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NRTS1260PFS, NRVTS1260PFS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current $(T_C = 161^{\circ}C)$	I _{F(AV)}	12	А
Peak Repetitive Forward Current, (T _C = 157°C, Square Wave, Duty = 0.5)	I _{FRM}	24	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	А
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature	T _J	-55 to +175	°C
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Assumes 600 mm², 1 oz. copper bond pad on a FR4 board)	$R_{ hetaJA}$	69	°C/W
Thermal Resistance, Junction-to-Case, Top (Assumes 600 mm², 1 oz. copper bond pad on a FR4 board)	$R_{\theta JCT}$	60	°C/W
Thermal Resistance, Junction-to-Case, Bottom (Assumes 600 mm², 1 oz. copper bond pad on a FR4 board)	$R_{ heta JCB}$	1.92	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Instantaneous Forward Voltage (Note 1) $ \begin{aligned} (I_F = 6 \text{ A, } T_J = 25^{\circ}\text{C}) \\ (I_F = 6 \text{ A, } T_J = 125^{\circ}\text{C}) \\ (I_F = 12 \text{ A, } T_J = 25^{\circ}\text{C}) \\ (I_F = 12 \text{ A, } T_J = 125^{\circ}\text{C}) \end{aligned} $	VF	0.50 0.43 0.58 0.55	- 0.66 0.64	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T _J = 25°C) (Rated dc Voltage, T _J = 125°C)	İR	7.5 5.1	350 60	μΑ mA
Junction Capacitance $(V_R = 1 \text{ V, } T_J = 25^{\circ}\text{C, 1 MHz})$	СЈ	1180	ı	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

NRTS1260PFS, NRVTS1260PFS

TYPICAL CHARACTERISTICS

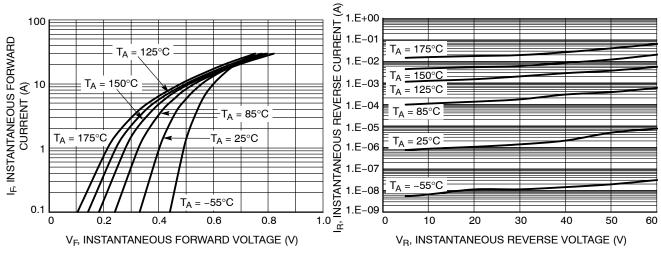


Figure 1. Typical Instantaneous Forward Characteristics

Figure 2. Typical Reverse Characteristics

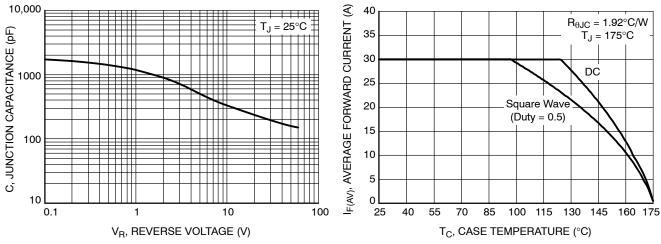


Figure 3. Typical Junction Capacitance

Figure 4. Current Derating

NRTS1260PFS, NRVTS1260PFS

TYPICAL CHARACTERISTICS

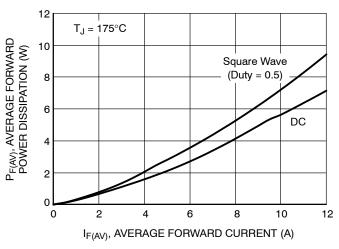


Figure 5. Forward Power Dissipation

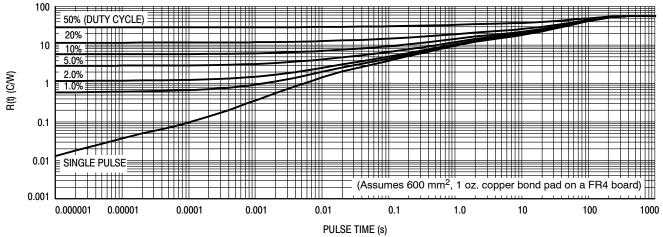


Figure 6. Typical Thermal Characteristics, Junction-to-Ambient

Κ

THP VIFW

В

E1

Α

Ε

TO-277-3LD CASE 340CZ ISSUE A

NDTES:

DATE 14 FEB 2020

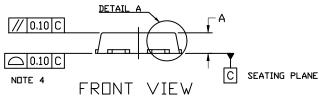


- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS b, b1,b2,b3,b6 AND c TO BE MEASURED ON FLAT SECTION OF THE LEAD, BETWEEN 0.13 AND 0.25mm FROM LEAD TIP.
- 4. COPLANARITY APPLES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
- 5. POSITIONAL TOLERANCE APPLIES TO THE TERMINALS AND EXPOSED PAD.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
- 7. DIMENSIONS D AND E TO BE DETERMINED AT DATUM PLANE C.

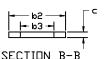
M°	
DETAIL A	
Δ	

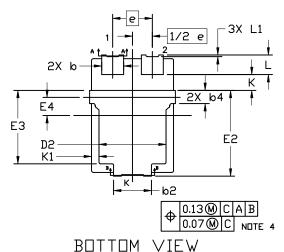
	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
Α	1.00	1.10	1.20
A1		0.01	0.05
b	1.13	1.18	1.28
b1	0.70 REF		
b2	1.98	2.03	2.13
b3	1.20 REF		
b4	0.71 REF		
U	0.20 REF		
D	4.45	4.60	4.75
D1	4.35	4.40	4.45
D2	3.50	3.60	3.70

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Ε	6.35	6.50	6.65	
E1	6.05	6.10	6.15	
E2	4.50	4.60	4.70	
E3	3.84	3.94	4.04	
E4	0.98 REF			
e	2.13 BSC			
K	0.85 REF			
K1	0.40 REF			
L	0.90	1.05	1.20	
L1	0.02			
М			12*	









	SECTION H H	SECTION D D
_	3.90 - - 2.33 -	
6.	3.90 80 4.60 2X 1.35 2.13 PITCH	2.84 3.50 4.90 2X 1.48
		5
	RECHMMENDET	

RECUMMENDED
MOUNTING FOOTPRINT

- For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.

GENERIC	
MARKING DIAGRAM	۷

XXXXXX = Specific Device Code

XXXXXX AWLYW A = Assembly Location Y = Year

W = Work Week
WL = Wafer Lot

DOCUMENT NUMBER:

Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

DESCRIPTION: TO-277-3LD

98AON97727G

PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

NRTS1260PFST3G NRVTS1260PFST3G